

INFRARED DIODE LASER AT 860nm

RN-H-860/1000~4000mW

产品描述

It features ultra compact design, long lifetime, cost-effectiveness and easy operation. They are used in measurement, communication, spectrum analysis, etc.

产品参数

RN-H-860/1000~4000mW	
Central wavelength (nm)	860±10
Operating mode	CW
Output power (mW)	>1000, 1100, 1200, ... , 4000
Power stability (rms, over 4 hours)	<1%, <2%, <3% (<0.5%, optional)
Transverse mode	Multimode
Dimensions of beam at the aperture (mm)	~5×8
Beam divergence, full angle (mrad)	<3.0
Warm-up time (minutes)	<5
Beam height from base plate (mm)	29
Operating temperature (°C)	10~35
Power supply (100-240VAC)	PSU-H-LED PSU-H-FDA
TTL / Analog modulation	TTL or Analog with 1Hz-1kHz 1kHz-10kHz, 10kHz-30kHz, 30kHz-100kHz optional
Expected lifetime (hours)	1 year
Warranty period	1 year